

FIG.1A

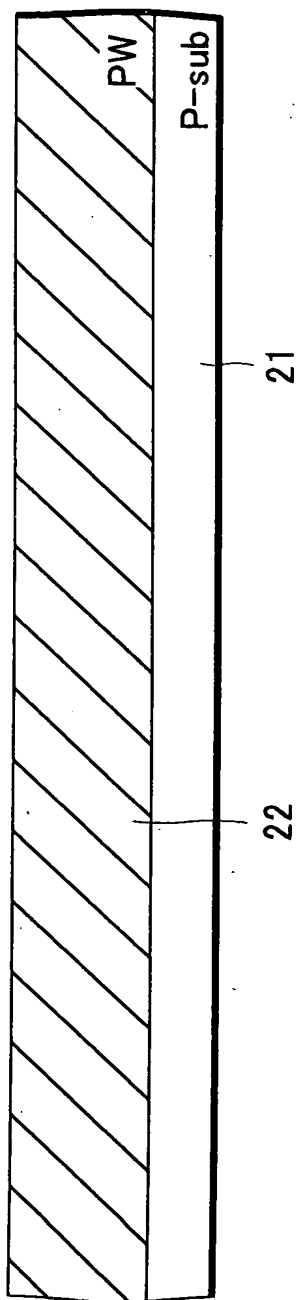


FIG.1B

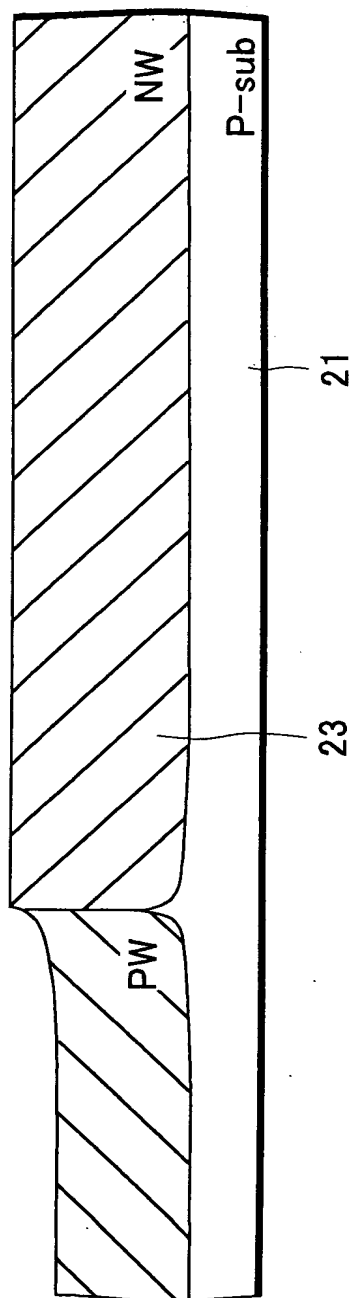


FIG.2A

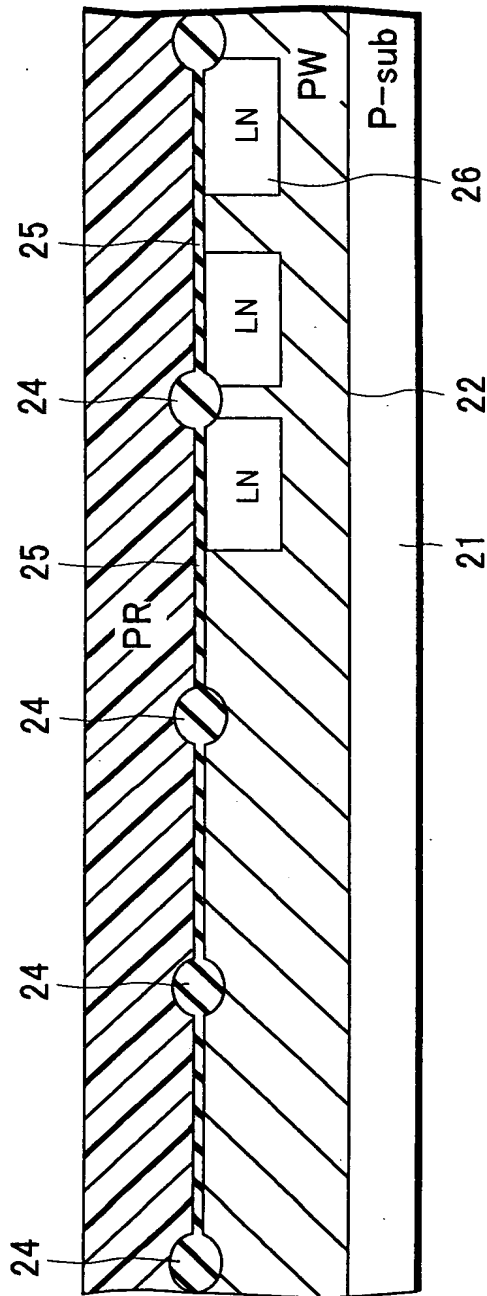


FIG.2B

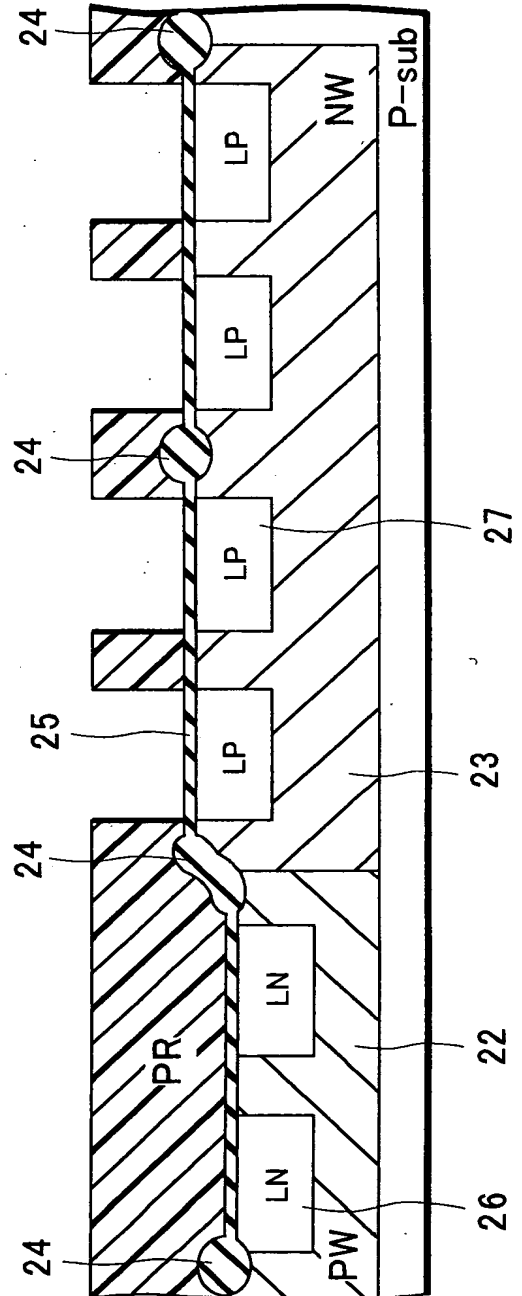


FIG.3A

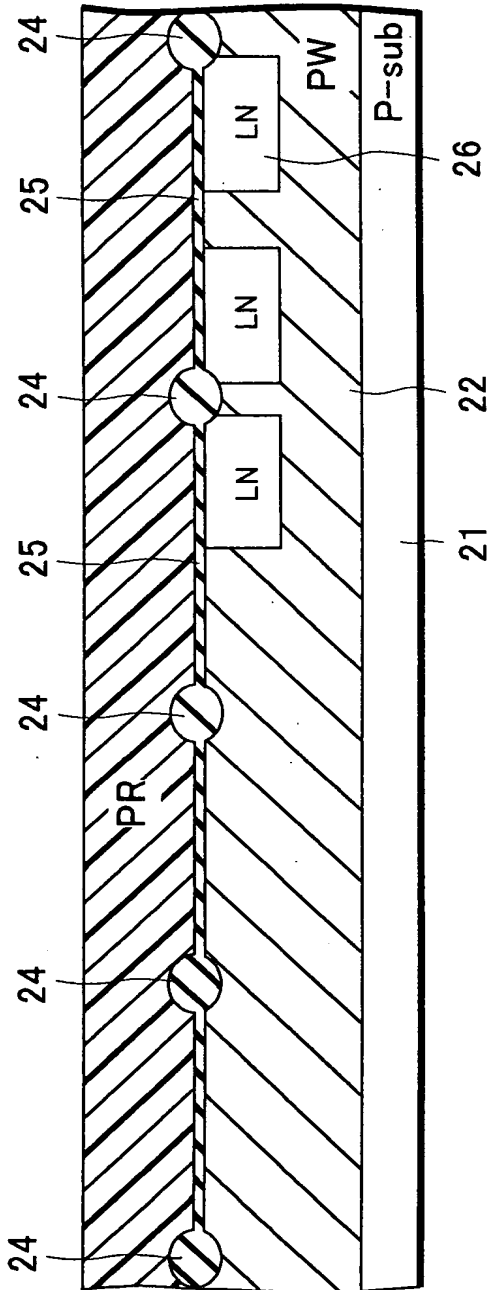


FIG.3B

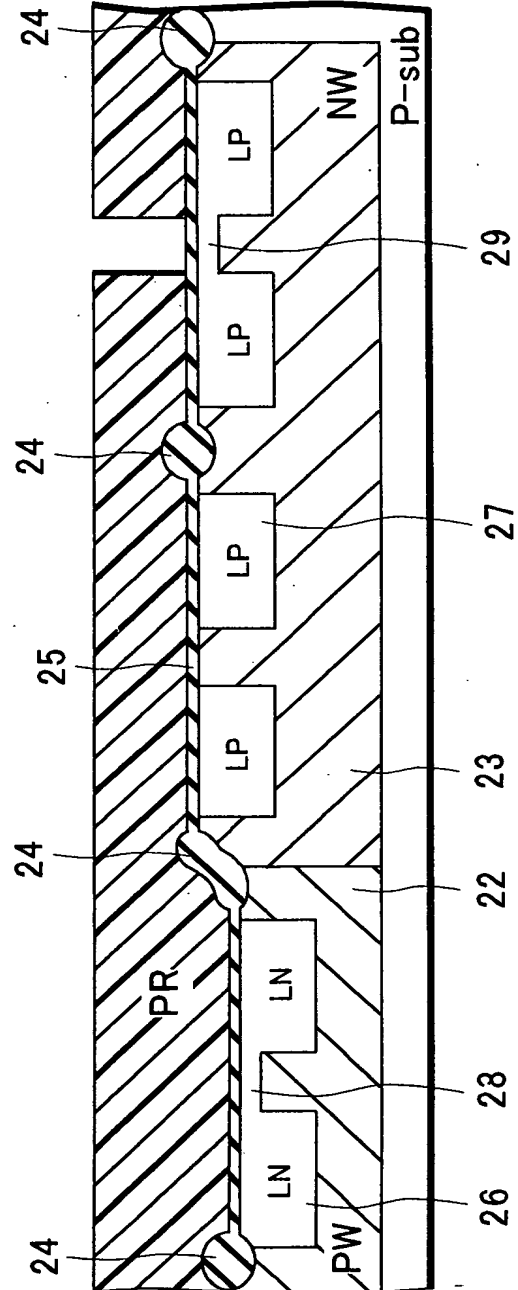


FIG. 4A

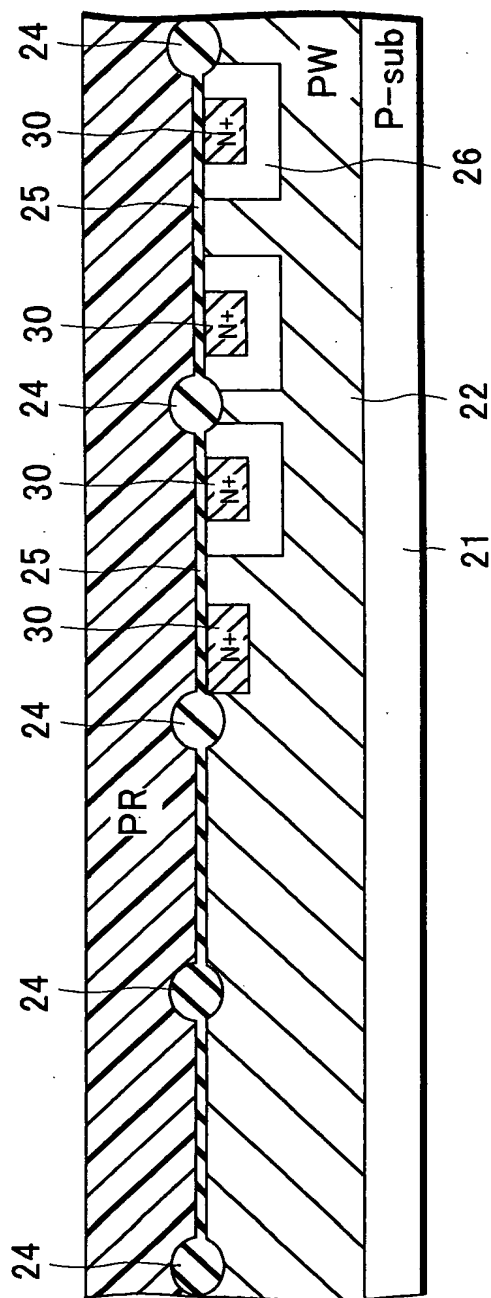


FIG. 4B

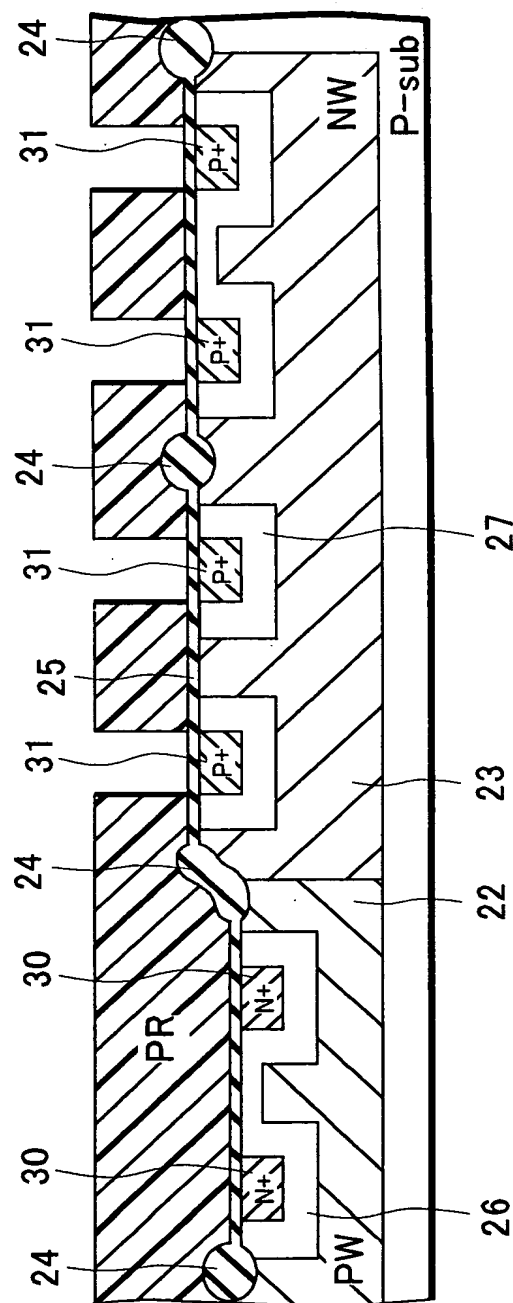


FIG.5A

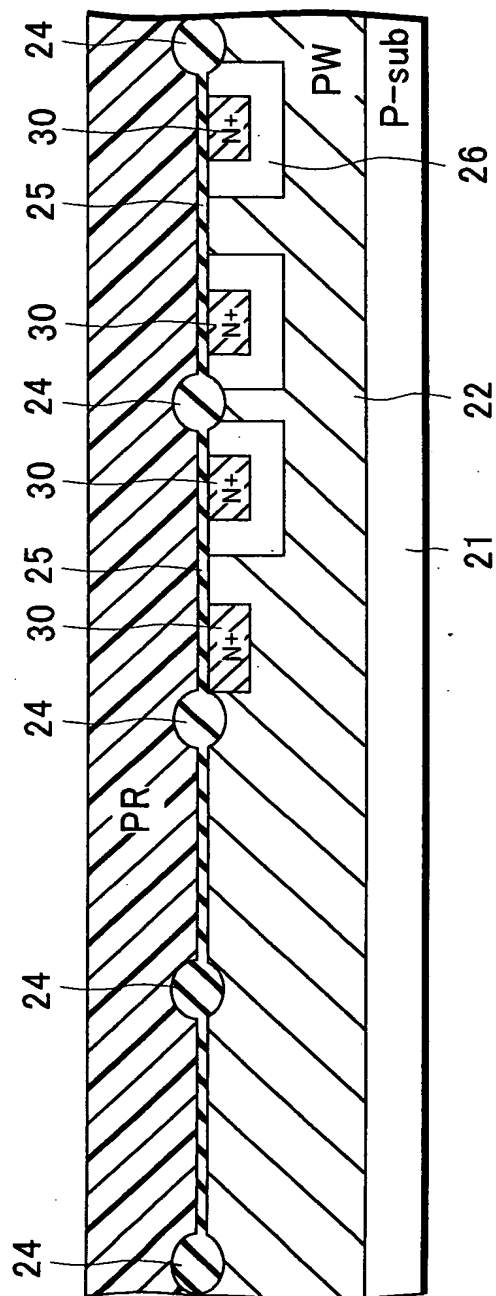


FIG.5B

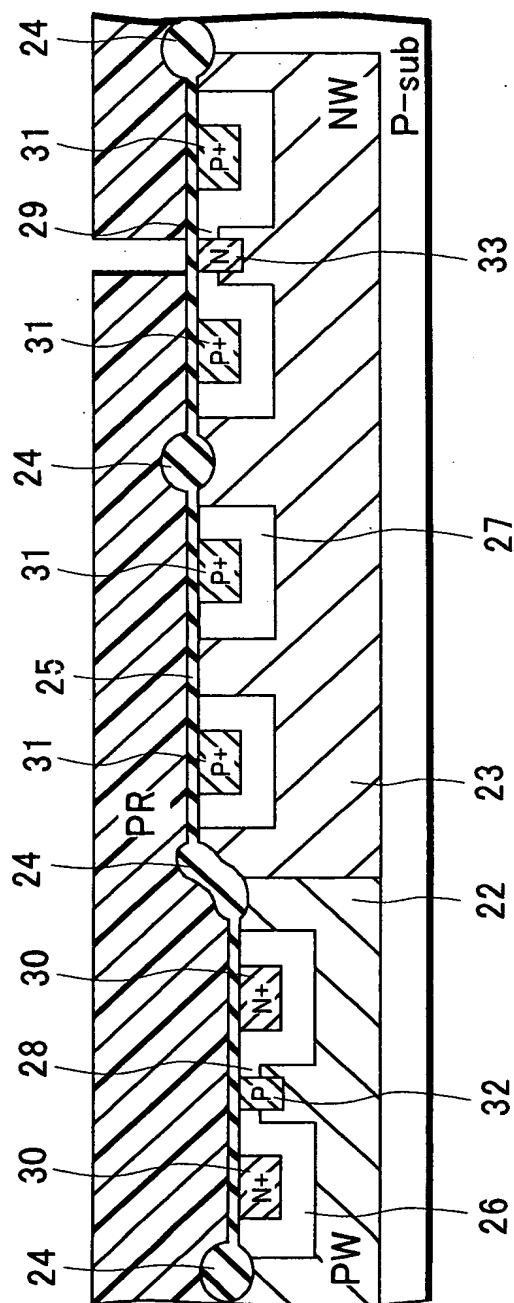


FIG.6A

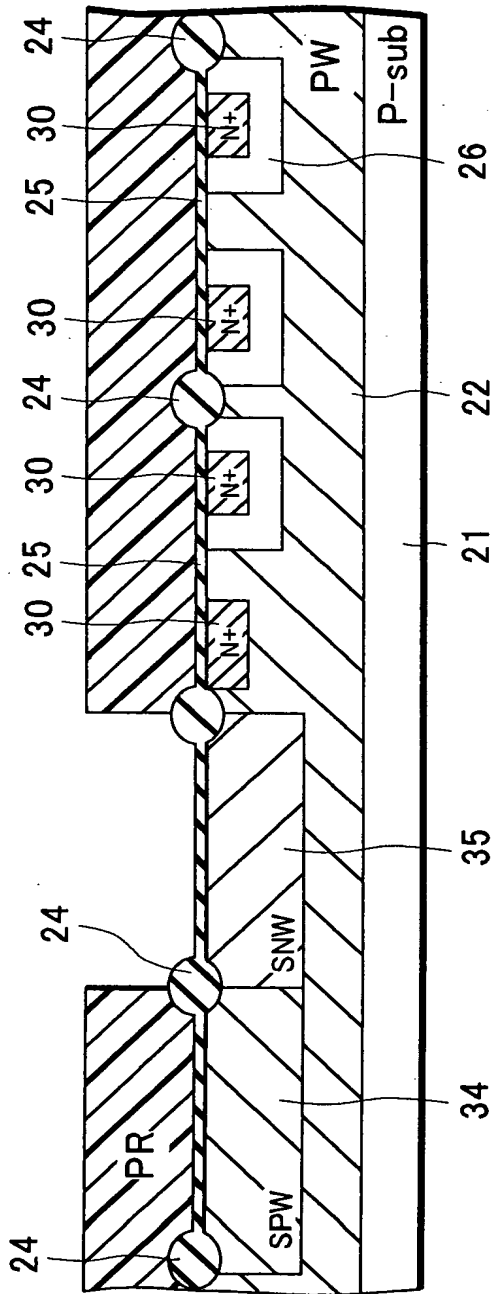


FIG.6B

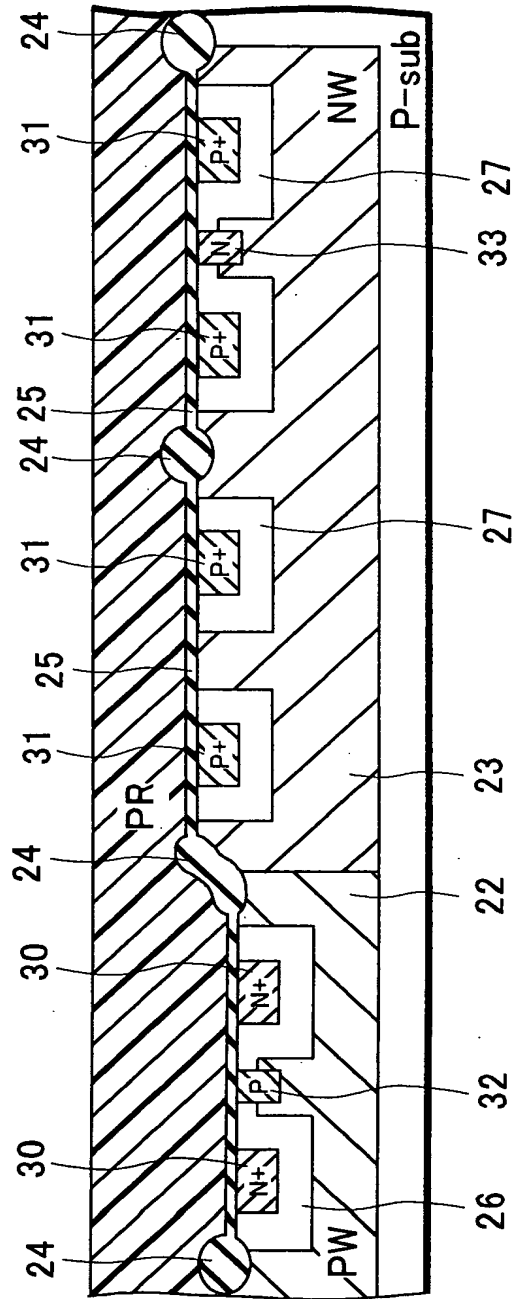


FIG. 7A

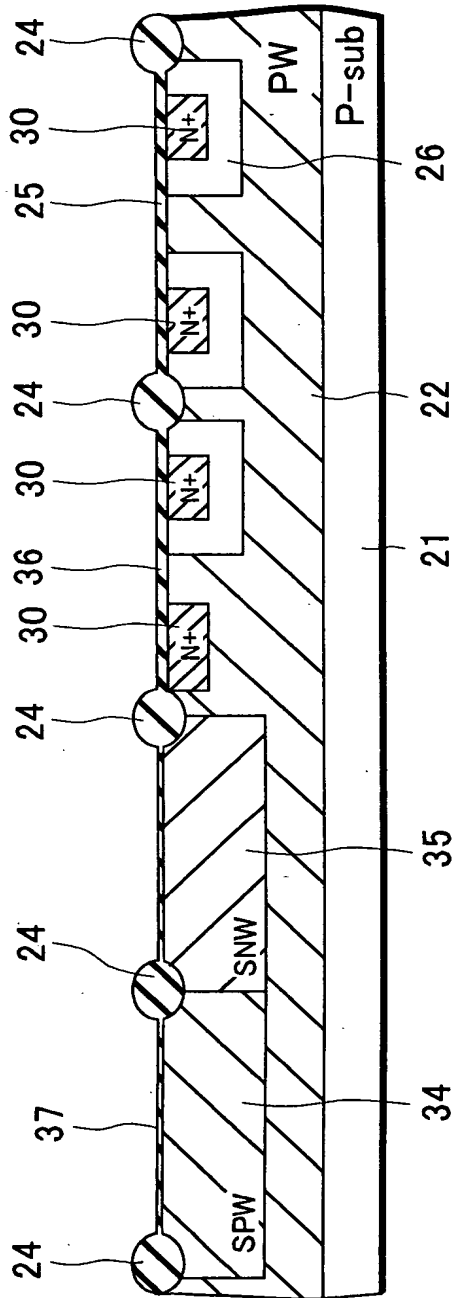


FIG. 7B

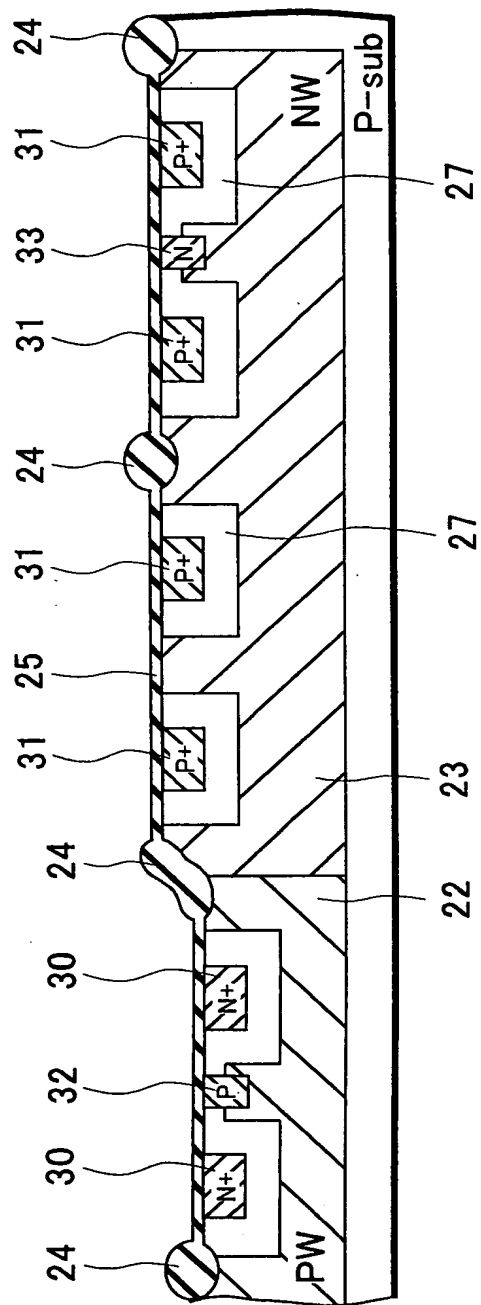


FIG.8A

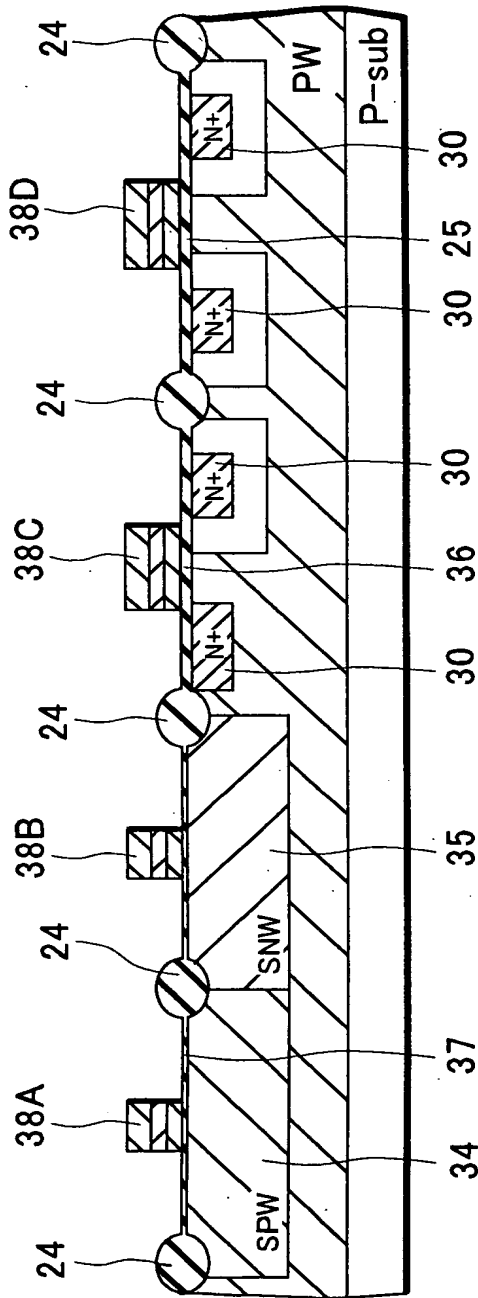


FIG.8B

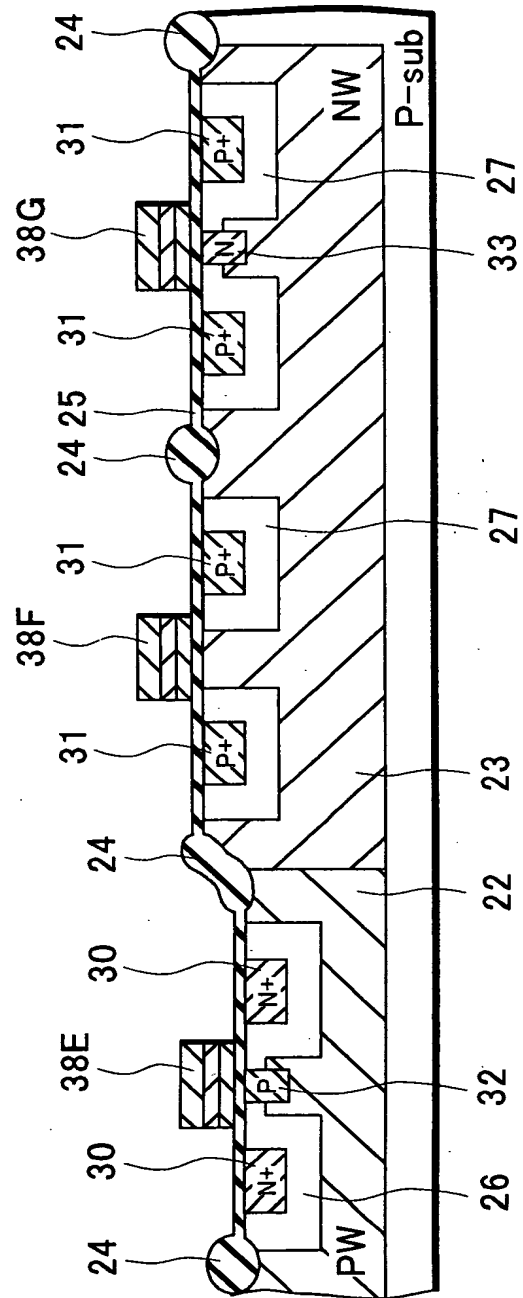


FIG.9A

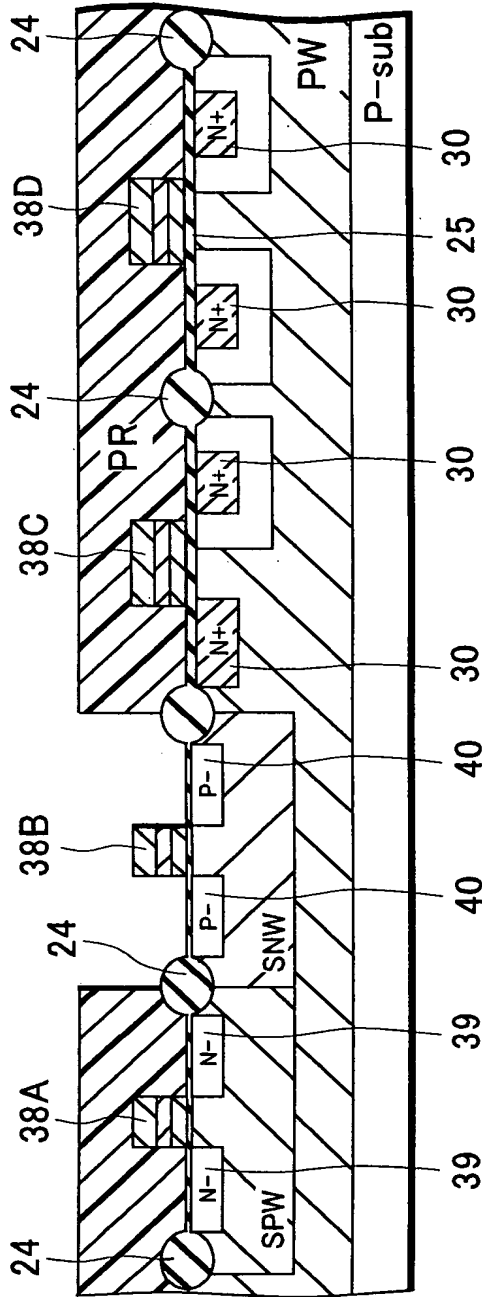
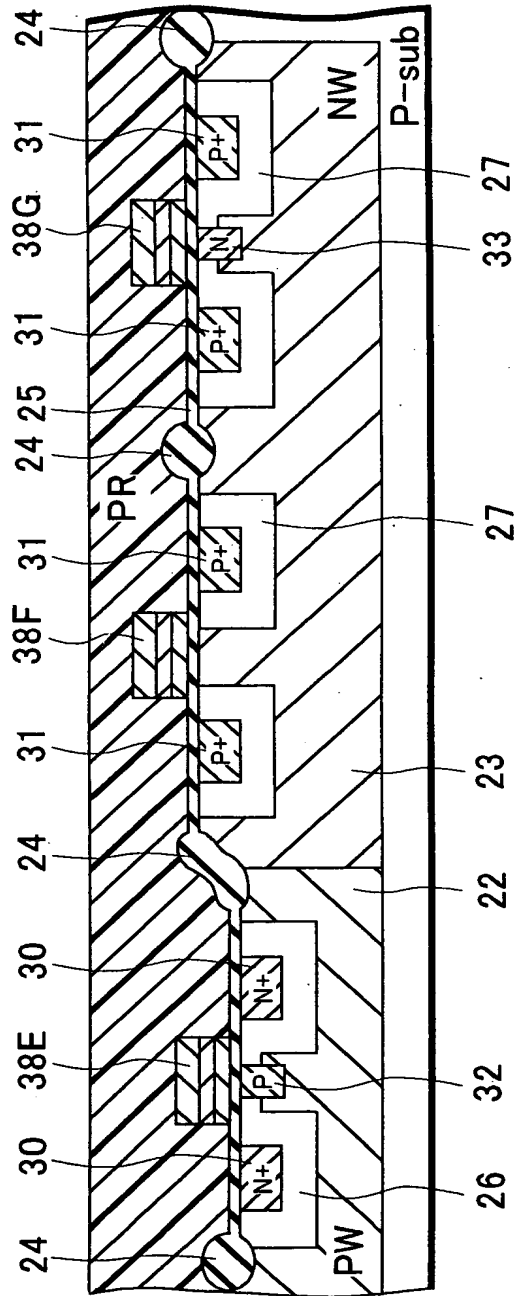


FIG.9B



[illegible]

This diagram shows a cross-sectional view of a semiconductor device. The structure consists of several layers and regions. At the top, there is a layer labeled 'P-sub'. Below this, there are several layers labeled 'NW' and 'PW'. The device is divided into several sections, each with a unique label: '38G', '38F', '38E', and '38D'. These sections are separated by regions labeled 'PR'. The device is also divided into several regions labeled 'P+', 'N+', and 'P-'. The regions are further divided into sub-regions labeled '24', '25', '26', '27', '28', '29', '30', '31', '32', '33', '34', '35', '36', '37', '38', '39', '40', and '41'. The device is shown in a cross-sectional view, with the layers and regions labeled with letters and numbers.

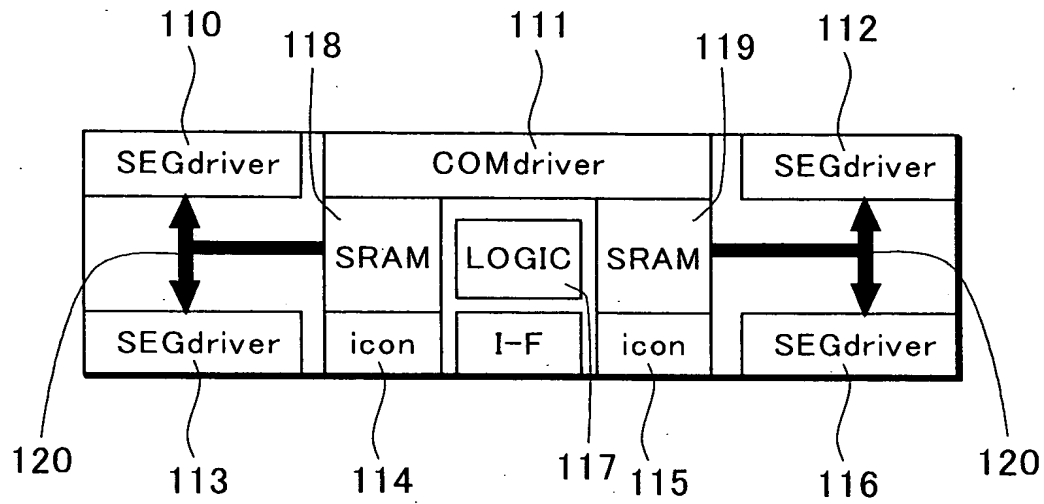
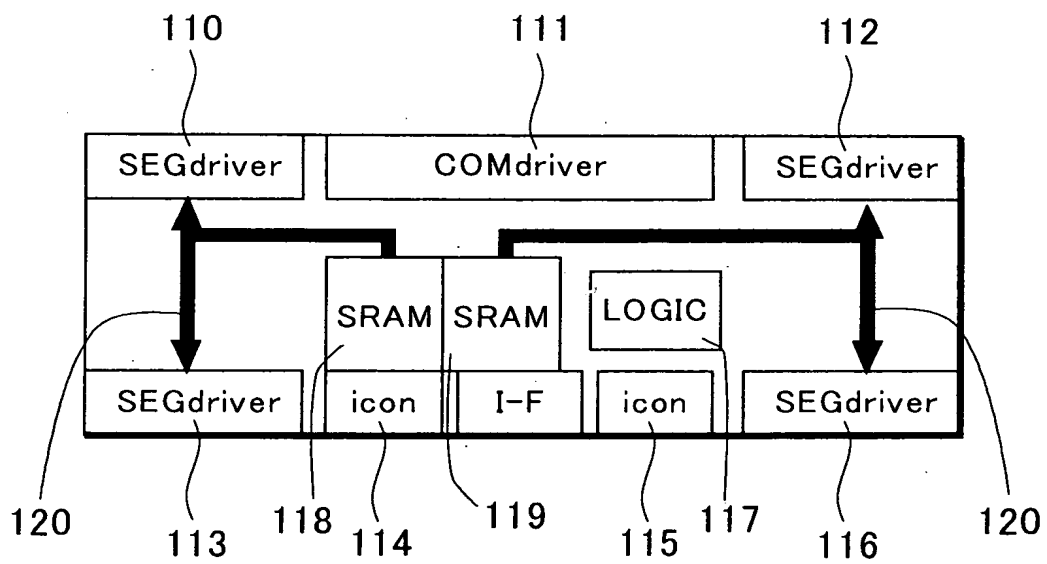
FIG.11A**FIG.11B**

FIG. 12

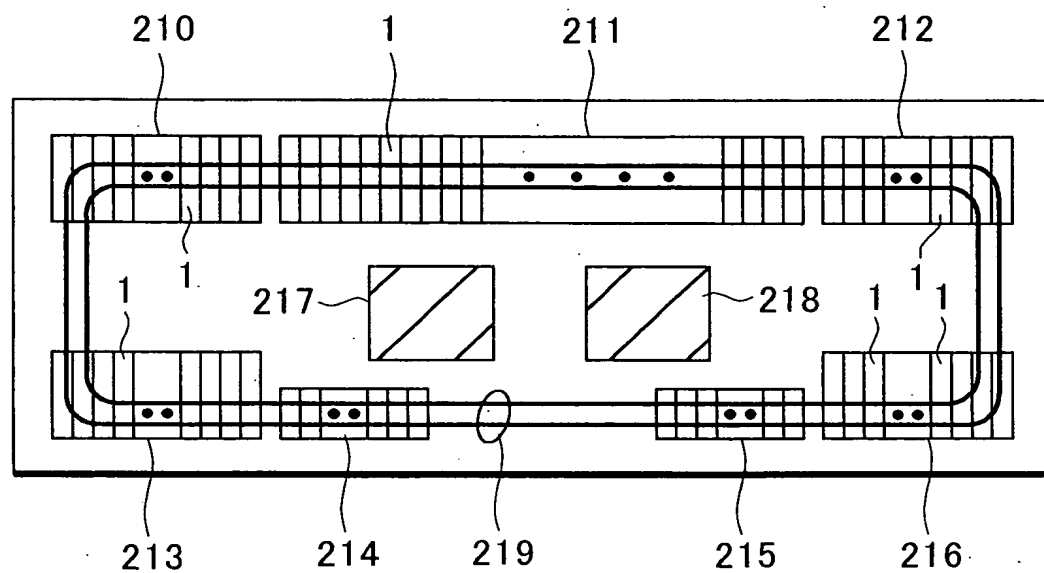


FIG. 13

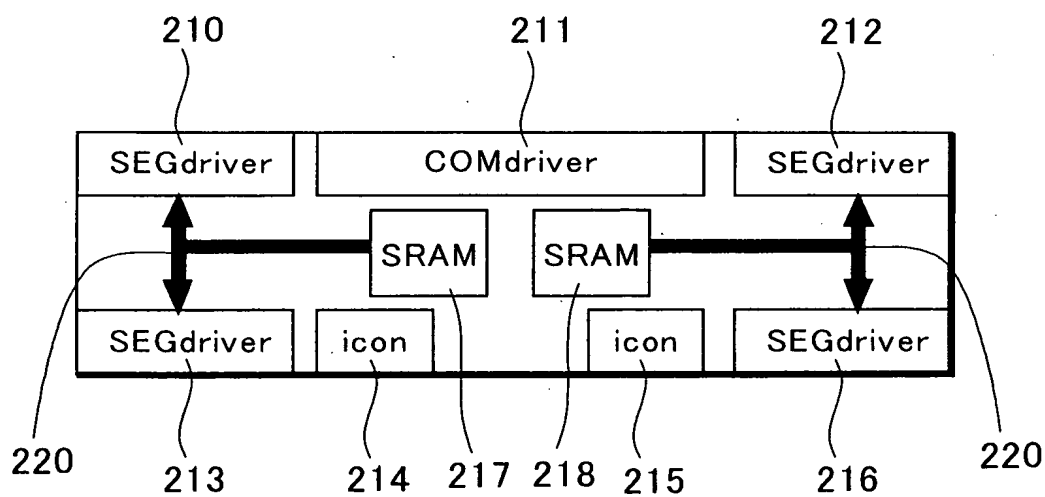


FIG. 14A

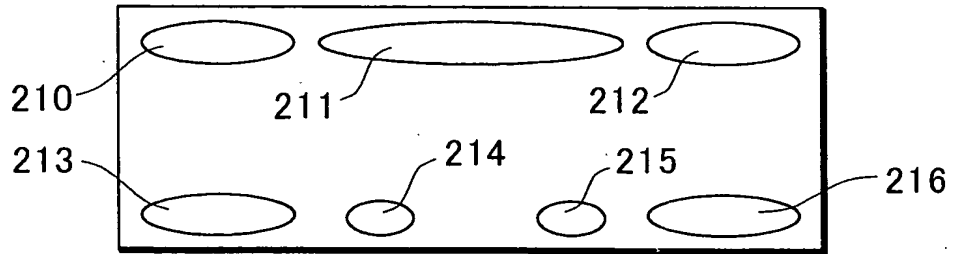


FIG. 14B

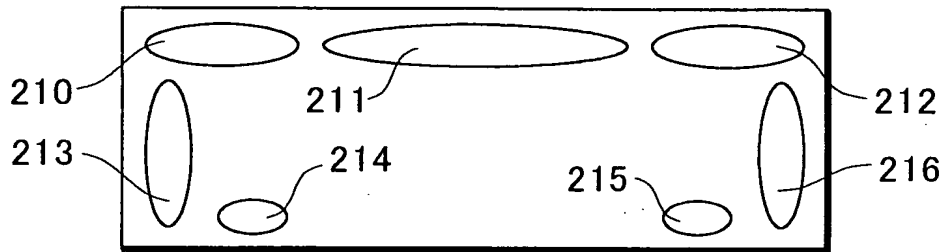


FIG. 14C

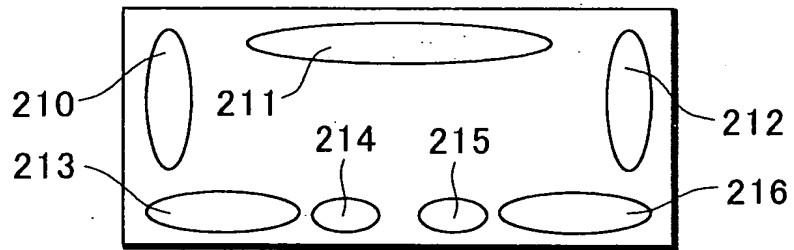


FIG. 14D

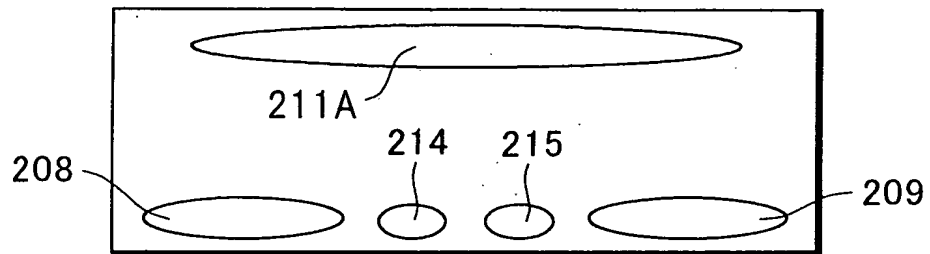


FIG. 15

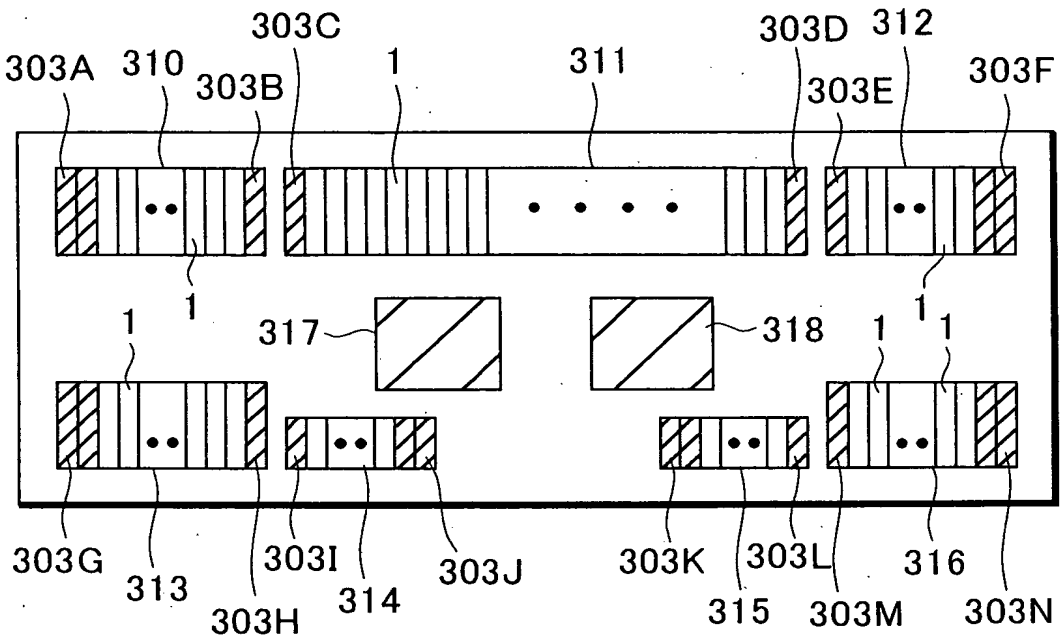


FIG. 16

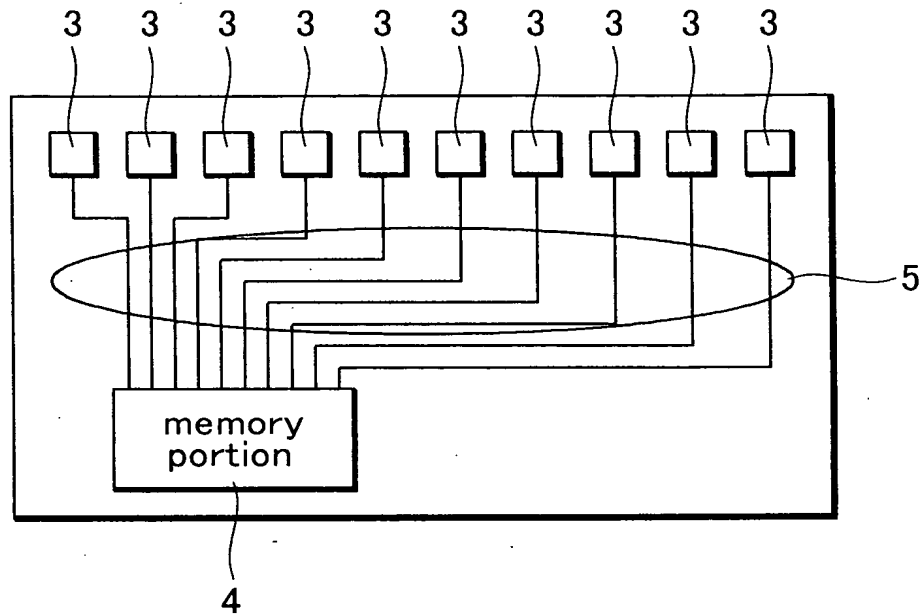


FIG.17A

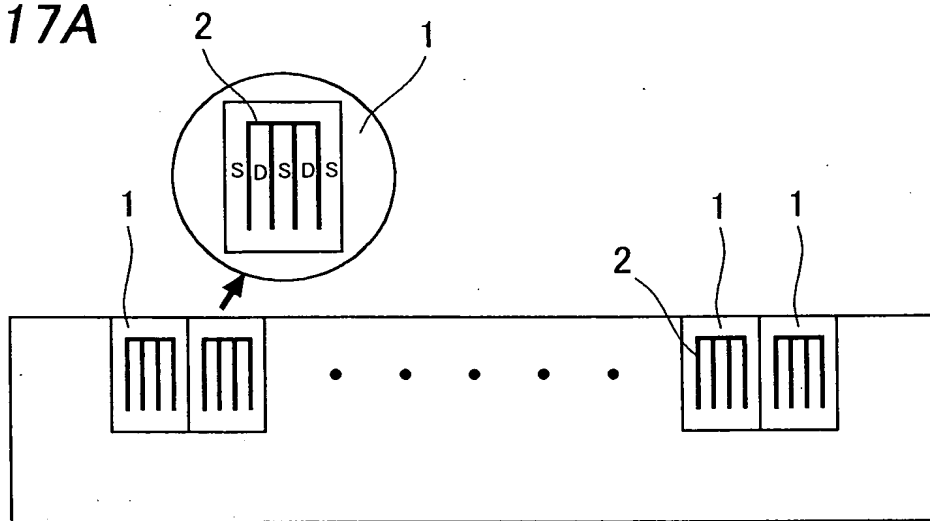


FIG.17B

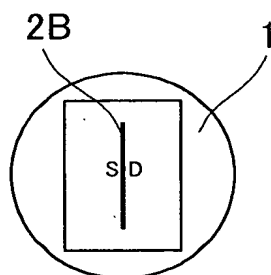


FIG.17C

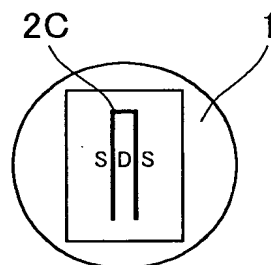


FIG.17D

